# **CNC7H001**

## Optoisolator

#### ■ Features

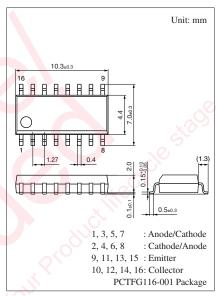
- Housed in a surface mount package alternative to mini-flat package of 1.27 mm pitch
- Double molded package
- 2.5 kV isolation voltage
- UL approved (File No. E79920)

#### ■ Applications

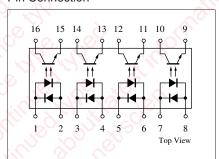
- Suited for interface circuits requiring high density mounting of parts, especially hybrid ICs and programmable controllers
- Signal transfer between circuits with different potentials and with impedances

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

	Symbol	Rating	Unit		
Input (light	Forward current (DC)	$I_F$	±50	mA	
emitting diode)	Pulse forward current *1	I <sub>FP</sub>	±1	A	
	Power dissipation *2	$P_{\mathrm{D}}$	75	mW/ch	
Output (photo	Collector current	$I_{C}$	50	mA	
transistor)	Collector-emitter voltage	V <sub>CEO</sub>	80	V	
	Emitter-collector voltage	V <sub>ECO</sub>	7 6	V	
	Collector power dissipation *3	$P_{C}$	120	mW/ch	
Isolation voltage, input to output *4		V <sub>ISO</sub>	2500	V[rms]	
Operating amb	Topr	-30 to +100	°C		
Storage temper	$T_{stg}$	-55 to +125	°C		



#### Pin Connection



Note) \*1: Pulse repetition rate = 100 pps. Pulse wide  $\leq$  100 µs

- \*2: Above 25°C ambient temperature, derate dissipation at the rate of 0.75 mW/°C.
- \*3: Above 25°C ambient temperature, derate dissipation at the rate of 1.2 mW/°C
- \*4: AC voltage (t = 1.0 min., RH < 60%)

### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

	Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input	Forward voltage	$V_{F}$	$I_F = \pm 50 \text{ mA}$		1.35	1.5	V
diode	Capacitance	C <sub>t</sub>	$V_R = 0 V, f = 1 MHz$		15		pF
Output	Collector-emitter dark current	$I_{CEO}$	$V_{CE} = 20 \text{ V}$		5	100	nA
transistor	Collector-emitter voltage	V <sub>CEO</sub>	$I_C = 100 \mu A$	80			V
	Emitter-collector voltage	V <sub>ECO</sub>	$I_E = 10 \mu A$	7			V
	Collector capacitance	$C_{C}$	$V_{CE} = 10 \text{ V}, \text{ f} = 1 \text{ MHz}$		10		pF
Coupled	Current transfer ratio *1	CTR	$V_{CE} = 5 \text{ V}, I_F = \pm 5 \text{ mA}$	100		600	%
	Capacitance	C <sub>ISO</sub>	f = 1 MHz		0.6		pF
	Resistance	R <sub>ISO</sub>	$V_{\rm ISO} = 500 \text{ V}$	1011			Ω
	Rise time *2	t <sub>r</sub>	$V_{CC} = 10 \text{ V}, I_{C} = 2 \text{ mA}$		4		μs
	Fall time *3	$t_{\rm f}$	$R_L = 100 \Omega$		3		
	Saturation voltage	V <sub>CE(sat)</sub>	$I_F = \pm 20 \text{ mA}, I_C = 1 \text{ mA}$		0.1	0.2	V
	Collector current ratio *4	I <sub>C(Ratio)</sub>	$V_{CE} = 5 \text{ V}, I_F = \pm 5 \text{ mA}$	0.33	1	3.0	_

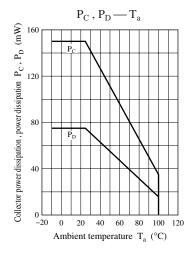
Note) \*1: CTR =  $I_C / I_F \times 100\%$ 

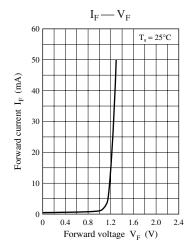
\*3: Fall time is defined as the time required for the collector current to decrease from 90% to 10% of peak value.

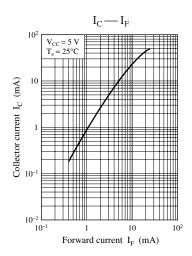
\*4: 
$$I_{C(Ratio)} = \frac{I_{C2} (I_F = I_{F2}, V_{CE} = 5 V)}{I_{C1} (I_F = I_{F1}, V_{CE} = 5 V)}$$

Input and output are practiced by electricity.

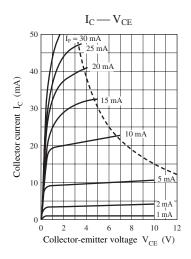
The device is designed be disregarded radiation.

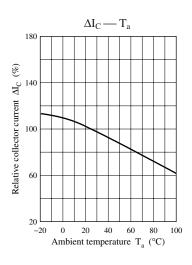


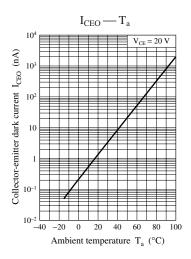


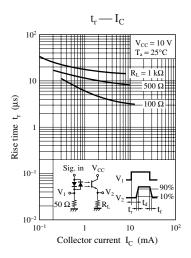


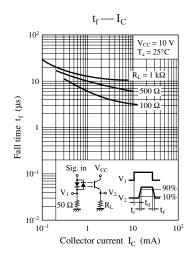
<sup>\*2:</sup> Rise time is defined as the time required for the collector current to rise from 10% to 90% of peak value.

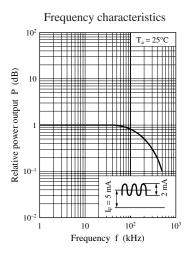












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